Structure	Silicon Monolithic Bipolar IC
Appearance	SIL-12 Pin Plastic Package (Power Type with Fin)
Application	Low Frequency Amplifier
Function	BTL 7.5W x 2ch Power Amplifier with Standby Function and Volume Function

A Absolute Maximum Ratings

No.	Item	Symbol	Ratings	Unit	Note
1	Storage Temperature	Tstg	-55 ~ +150	° C	1
2	Operating Ambient Temperature	Topr	-25 ~ +70	° C	1
3	Operating Ambient Pressure	Popr	$1.013x10^5 \pm 0.61x10^5$	Pa	
4	Operating Constant Acceleration	Gopr	9,810	m/s^2	
5	Operating Shock	Sopr	4,900	m/s^2	
6	Supply Voltage	Vcc	24	V	2
7	Supply Current	Icc	4.0	A	
8	Power Dissipation	P_D	37.5	W	Ta=70°C

Operating Supply Voltage Range	Vcc	5V ~ 18V

Note 1) The temperature of all items shall be Ta=25°C except storage temperature and operating ambient temperature.

2) At no signal input.

B Electrical Characteristics

(Unless otherwise specified, the ambient temperature is 25°C±2°C, Vcc=12V, frequency=1kHz and R_L=8Ω.)

No	Item	Symbol	Test Circuit	Conditions	Limits min	Limits typ	Limits max	Unit	Note
1	Quiescent Circuit Current	I_{CQ}	1	Vin=0V, Vol=0V	-	45	100	mA	
2	Standby Current	I_{STB}	1	Vin=0V, Vol=0V	-	1	10	μA	
3	Output Noise Voltage	V_{NO}	1	Rg=10kΩ, Vol=0V	-	0.2	0.6	mVrms	1
4	Voltage Gain	G_V	1	Po=1.0W, Vol=1.25V	38	40	42	dB	
5	Total Harmonic Distortion	THD	1	Po=1.0W, Vol=1.25V	-	0.10	0.5	%	
6	Maximum Power Output 1	P_O1	1	THD=10%, Vol=1.25V	6.0	7.5	-	W	
7	Maximum Power Output 2	P_O2	1	Vcc=15V THD=10%, Vol=1.25V	10.0	12.5	-	W	
8	Ripple Rejection Ratio	RR	1	Rg=10kΩ, Vol=0V Vr=1Vrms, fr=120Hz	30	50	-	dB	1
9	Output Offset Voltage	Voff	1	Rg=10kΩ, Vol=0V	-350	0	350	mV	
10	Volume Attenuation Ratio	Att	1	Po=1.0W, Vol=0V	70	80	-	dB	1
11	Channel Balance 1	CB1	1	Po=1.0W, Vol=1.25V	-1	0	1	dB	
12	Channel Balance 2	CB2	1	Po=1.0W, Vol=0.6V	-2	0	2	dB	
13	Middle Voltage Gain	G_{Vm}	1	Po=1.0W, Vol=0.6V	26.5	29.5	32.5	dB	
14	Channel Crosstalk	CT	1	Po=1.0W, Vol=1.25V	40	55	-	dB	

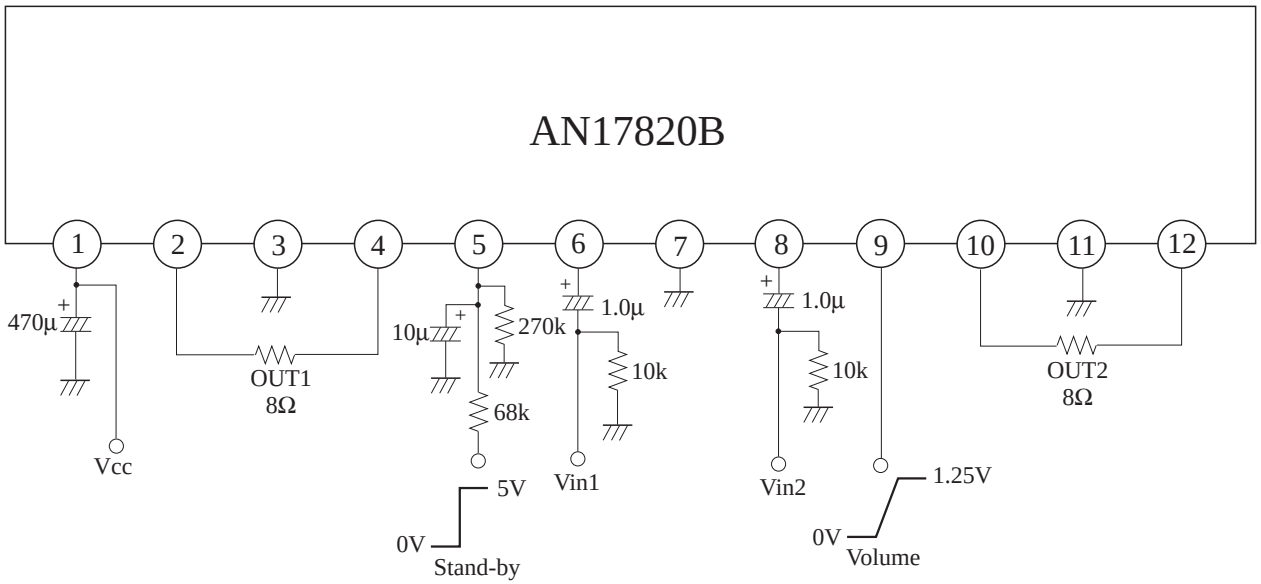
Note 1) For this measurement, use the BPF = 15Hz ~ 30kHz (12dB/OCT).

B	Electrical Characteristics	(Unless otherwise specified, the ambient temperature is 25°C±2°C, Vcc=12V, frequency=1kHz and R_L=8Ω.)							
No	Item	Symbol	Test Circuit	Conditions	Limits			Unit	Note
					min	typ	max		
1	Standby pin current	I_{STB2}	1	Vin=0V, V_{STB}=3V	-	-	25	µA	
2	Volume pin current	I_{VOL}	1	Vin=0V, Vol=0V	-12	-	-	µA	
3	Input Impedance	Z_i	1	Vin=±0.3V_{DC}	24	30	36	kΩ	

Note) The above characteristics are reference values determined for IC design, but not guaranteed values for shipping inspection. If problems were to occur, counter measures will be sincerely discussed.

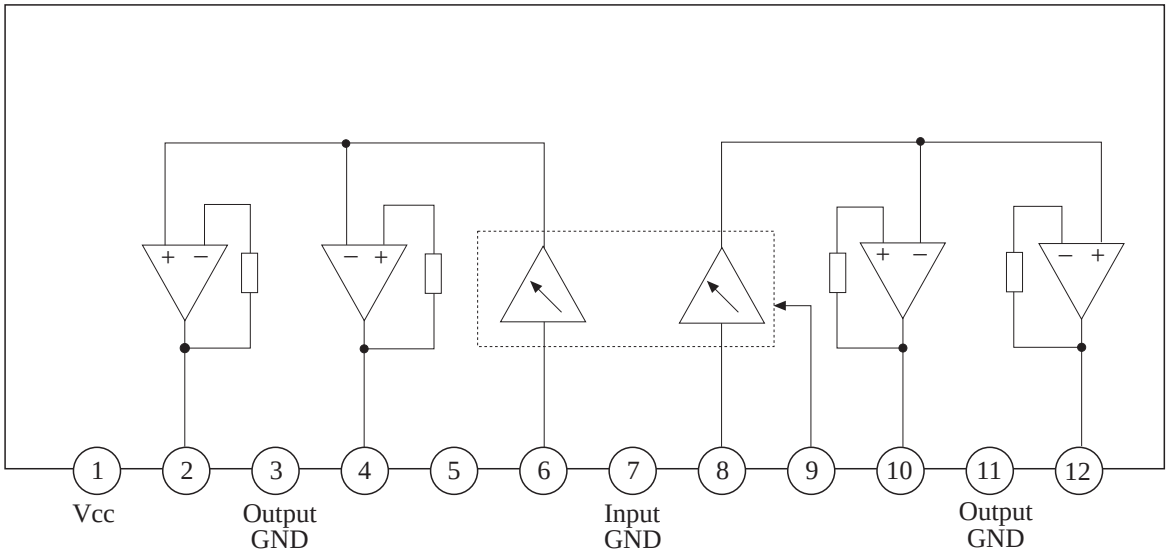
(Description of test circuit and test method)

Test Circuit 1



Note) If the standby pin is open or 0V, the IC is on standby state.
The IC is in the state of volume minimum if the Volume pin is ground.
The IC is in the state of volume maximum if the Volume pin is open.

Circuit Function Block Diagram



Pin Descriptions

Pin No.	Description	Pin No.	Description
1	Vcc	7	GND (Input)
2	Ch.1 Output (+)	8	Ch.2 Input
3	GND (Ch.1 Output)	9	Volume
4	Ch.1 Output (-)	10	Ch.2 Output (-)
5	Standby	11	GND (Ch.2 Output)
6	Ch.1 Input	12	Ch.2 Output (+)

Prepared		Product Specifications	Ref No.	E
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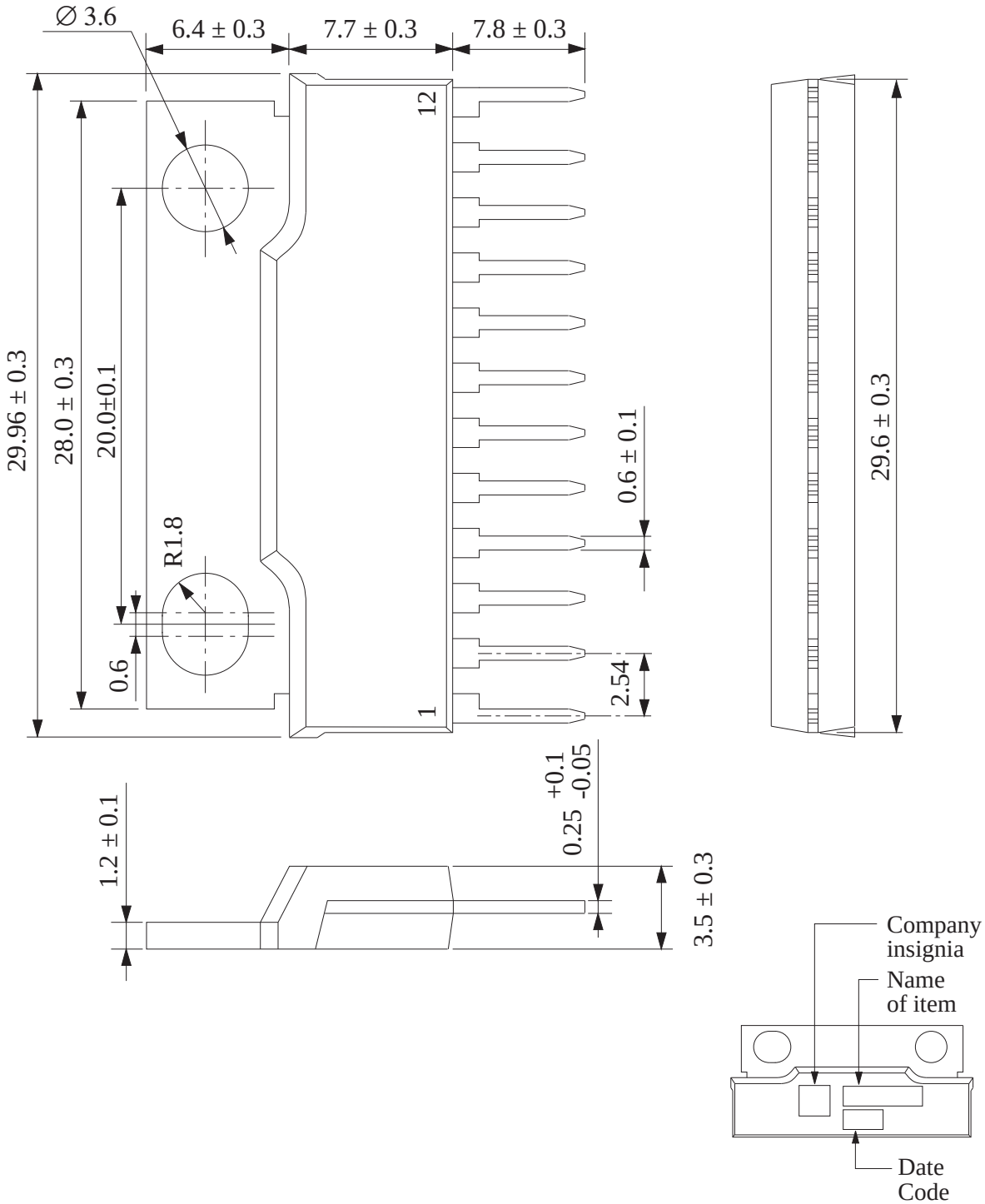
Package Name	FP-12S

Unit : mm

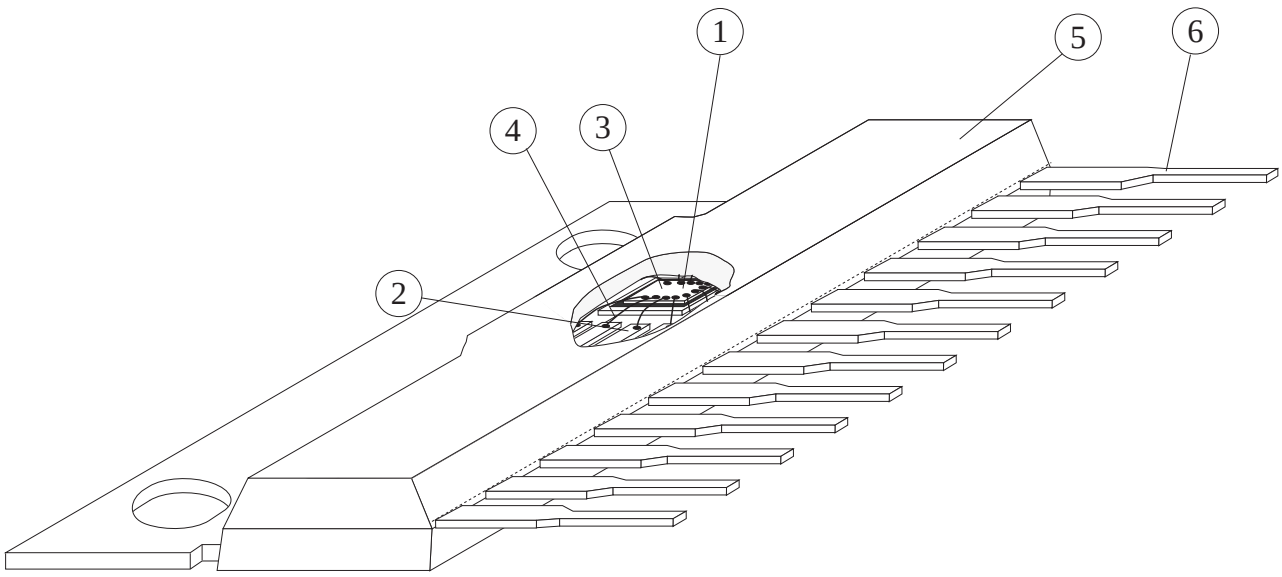


Eff. Date	Eff. Date	Eff. Date	Eff. Date
09-JUL-2001			

(Structure Description)

Chip surface passivation	[SiN,]	PSG,	Others ( )	(1)
Lead frame material	Fe group,	[Cu group,]	Others ( )	(2), (6)
Inner lead surface process	[Ag plating,]	Au plating,	Others ( )	(2)
Outer lead surface process	Solder plating,	[Solder dip,]	Others ( )	(6)
Chip mounting method	Ag paste,	Au-Si alloy, [Solder,]	Others ( )	(3)
Wire bonding method	[Thermalsonic bonding,]		Others ( )	(4)
Wire material, Diameter	[Au,]	Diameter 38 μm	Others ( )	(4)
Mold material	[Epoxy,]		Others ( )	(5)
Molding method	[Transfer mold,]	Multiplunger mold,	Others ( )	(5)
Fin material	[Cu Group]		Others ( )	(7)

Package FP-12S



PD - Ta Curves

(1) Tc = Ta, 62.5W (θj-c = 2 °C/W)

(2) 20.83W (θf = 4.0 °C/W)

With a 100cm^2 X 3mm Al heat sink (black colour coated)

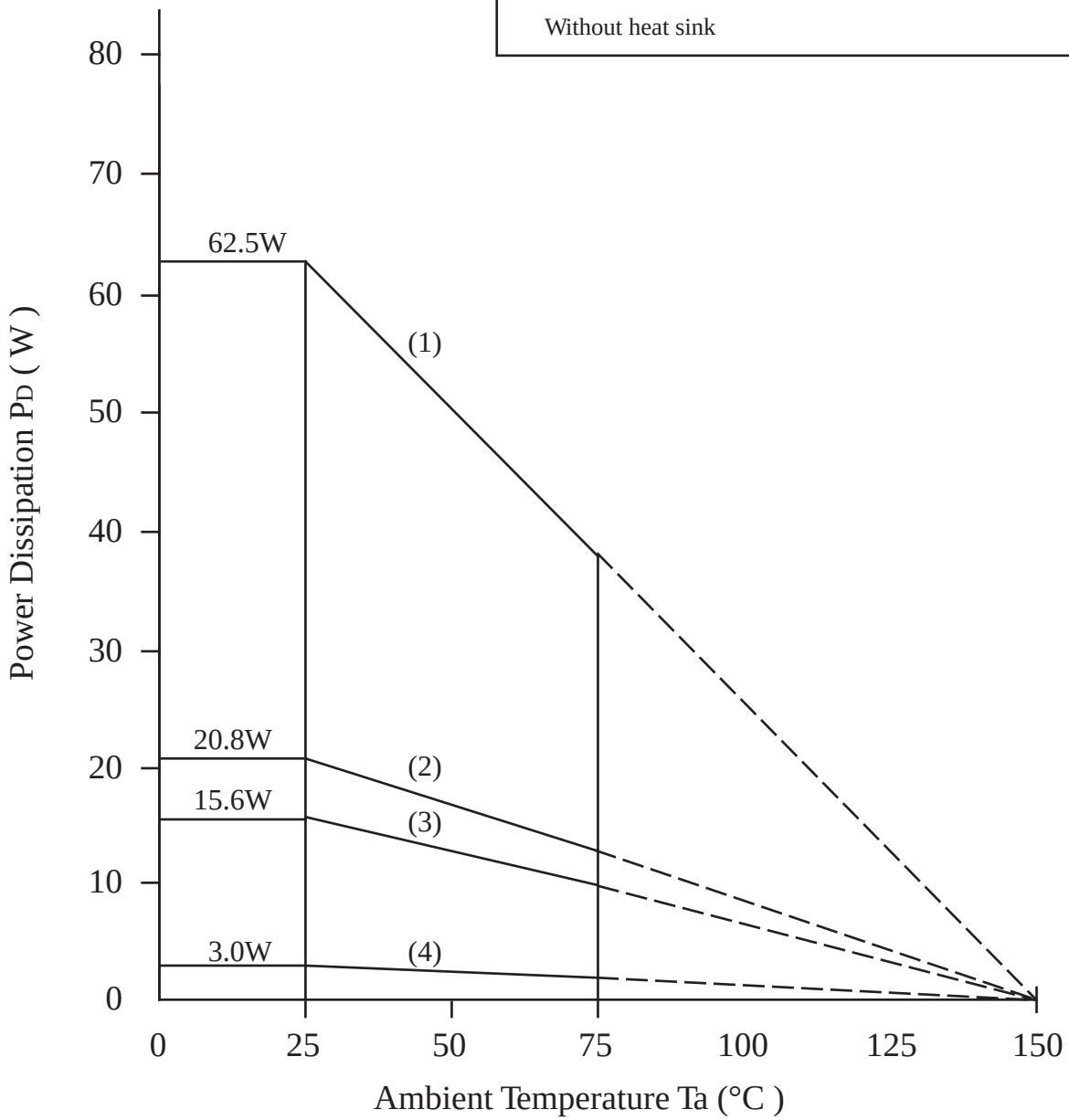
or a 200cm^2 X 2mm Al heat sink (not lacquered)

(3) 15.63W (θf = 6.0 °C/W)

With a 100cm^2 X 2mm Al heat sink (not lacquered)

(4) 3.0W at Ta = 25°C (θj-a = 42 °C/W)

Without heat sink



(Precautions for use)

1) Make sure that the IC is free of any pin short-circuiting, ground short, and load short-circuiting.

2) Ground the radiation fin so that there will be no difference in electric potential between the radiation fin and ground.

3) The thermal protection circuit operates at a Tj of approximately 150°C. The thermal protection circuit is reset automatically when the temperature drops.

4) Make sure that the heat radiation design is effective enough if the Vcc is comparatively high or the IC operates high output power.

5) Connect only ground pin for signal sources to the signal GND pin of the amplifier on the previous stage.